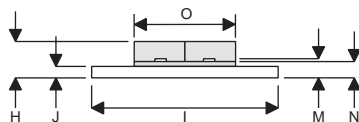
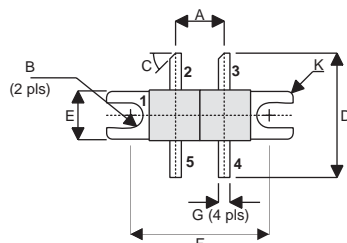


MECHANICAL DATA



DK

PIN 1 SOURCE (COMMON) PIN 2 DRAIN 1
 PIN 3 DRAIN 2 PIN 4 GATE 2
 PIN 5 GATE 1

DIM	mm	Tol.	Inches	Tol.
A	6.45	0.13	0.254	0.005
B	1.65R	0.13	0.065R	0.005
C	45°	5°	45°	5°
D	16.51	0.76	0.650	0.03
E	6.47	0.13	0.255	0.005
F	18.41	0.13	0.725	0.005
G	1.52	0.13	0.060	0.005
H	5.08	max	0.200	max
I	24.76	0.13	0.975	0.005
J	1.52	0.13	0.060	0.005
K	0.81R	0.13	0.032R	0.005
M	0.10	0.02	0.004	0.001
N	2.16	0.13	0.085	0.005
O	12.80	max	0.504	max

**GOLD METALLISED
 MULTI-PURPOSE SILICON
 DMOS RF FET
 40W – 12.5V – 500MHz
 PUSH-PULL**

FEATURES

- SIMPLIFIED AMPLIFIER DESIGN
- SUITABLE FOR BROAD BAND APPLICATIONS
- LOW C_{rss}
- SIMPLE BIAS CIRCUITS
- LOW NOISE
- HIGH GAIN – 10 dB MINIMUM

APPLICATIONS

- HF/VHF/UHF COMMUNICATIONS
 from 1 MHz to 500 MHz

ABSOLUTE MAXIMUM RATINGS ($T_{case} = 25^{\circ}C$ unless otherwise stated)

P_D	Power Dissipation	175W
BV_{DSS}	Drain – Source Breakdown Voltage*	40V
BV_{GSS}	Gate – Source Breakdown Voltage*	$\pm 20V$
$I_{D(sat)}$	Drain Current*	20A
T_{stg}	Storage Temperature	-65 to $150^{\circ}C$
T_j	Maximum Operating Junction Temperature	$200^{\circ}C$

* Per side

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ELECTRICAL CHARACTERISTICS (T_{case} = 25°C unless otherwise stated)

Parameter	Test Conditions	Min.	Typ.	Max.	Unit
PER SIDE					
B _V DSS	Drain-Source Breakdown Voltage	V _{GS} = 0 I _D = 100mA	40		V
I _D DSS	Zero Gate Voltage Drain Current	V _{DS} = 12.5V V _{GS} = 0		2	mA
I _G DSS	Gate Leakage Current	V _{GS} = 20V V _{DS} = 0		1	μA
V _{GS(th)}	Gate Threshold Voltage*	I _D = 10mA V _{DS} = V _{GS}	1	7	V
g _{fs}	Forward Transconductance*	V _{DS} = 10V I _D = 2A	1.6		S
TOTAL DEVICE					
G _{PS}	Common Source Power Gain	P _O = 40W	10		dB
η	Drain Efficiency	V _{DS} = 12.5V I _{DQ} = 1.6A	50		%
VSWR	Load Mismatch Tolerance	f = 400MHz	20:1		—
PER SIDE					
C _{iss}	Input Capacitance	V _{DS} = 0V V _{GS} = -5V f = 1MHz		120	pF
C _{oss}	Output Capacitance	V _{DS} = 12.5V V _{GS} = 0 f = 1MHz		80	pF
C _{rss}	Reverse Transfer Capacitance	V _{DS} = 12.5V V _{GS} = 0 f = 1MHz		8	pF

* Pulse Test: Pulse Duration = 300 μs , Duty Cycle ≤ 2%

HAZARDOUS MATERIAL WARNING

The ceramic portion of the device between leads and metal flange is beryllium oxide. Beryllium oxide dust is highly toxic and care must be taken during handling and mounting to avoid damage to this area.

THESE DEVICES MUST NEVER BE THROWN AWAY WITH GENERAL INDUSTRIAL OR DOMESTIC WASTE.

THERMAL DATA

R _{THj-case}	Thermal Resistance Junction – Case	Max. 1.0°C / W
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Document Number 3204

Issue 3

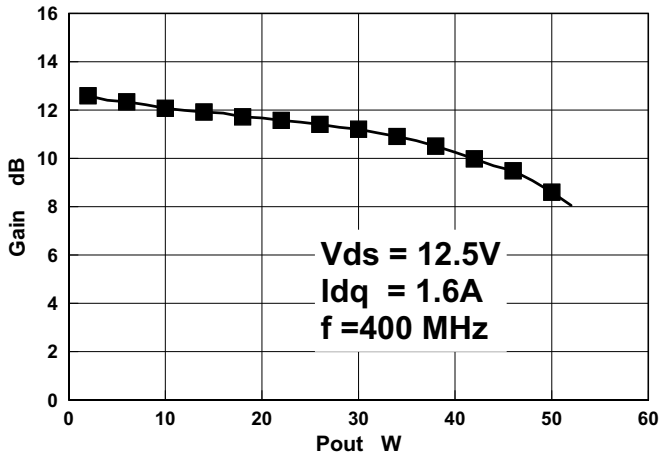


Figure 1- Gain vs. Power Output

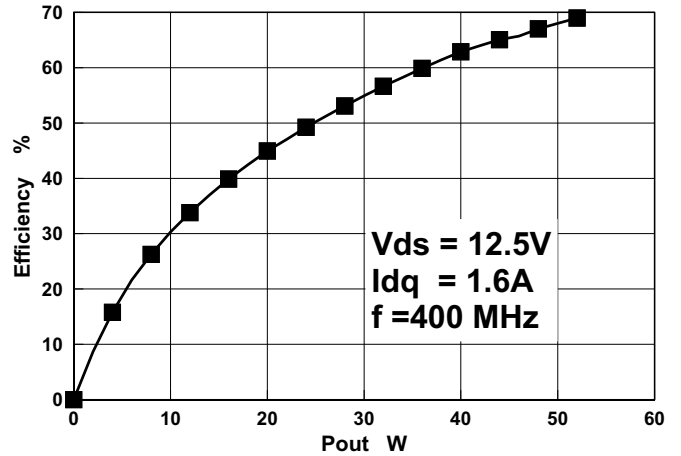


Figure 2 - Efficiency vs. Power Output

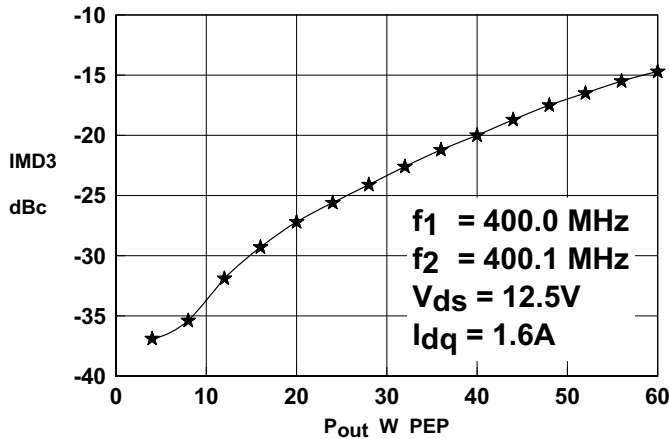


Figure 3 - IMD vs. Power Output

OPTIMUM SOURCE AND LOAD IMPEDANCE

Frequency MHz	Z _S Ω	Z _L Ω
400	1.5 + j1.2	1.9 - j1.1

Typical S Parameters

! V_{DS} = 12.5V, I_{DQ} = 0.4A
MHz S MA R 50

Freq MHz	S11		S21		S12		S22	
	mag	ang	mag	ang	mag	ang	mag	ang
70	0.71	-151.2	9.5	73.1	0.019	-9.1	0.77	-163.9
100	0.75	-156.2	6.1	62.2	0.016	-13.2	0.79	-166.0
150	0.81	-162.7	3.7	50.4	0.012	-12.8	0.83	-169.7
200	0.85	-167.4	2.4	44.0	0.009	0.4	0.86	-172.8
250	0.88	-171.0	1.7	36.6	0.008	20.8	0.88	-175.3
300	0.90	-173.9	1.3	34.5	0.009	49.0	0.89	-176.6
350	0.91	-175.1	1.0	26.0	0.010	60.6	0.90	-178.7
400	0.92	-177.9	0.8	23.4	0.014	70.2	0.91	-180.0
450	0.93	-179.7	0.7	17.6	0.017	75.0	0.92	-178.6
500	0.93	178.1	0.6	13.3	0.021	77.9	0.93	176.8
550	0.94	175.9	0.5	8.2	0.023	78.5	0.93	175.4
600	0.95	174.2	0.4	2.5	0.028	77.1	0.94	174.4
650	0.95	172.2	0.3	8.9	0.029	80.6	0.95	172.9
700	0.96	170.9	0.2	19.2	0.034	76.8	0.95	171.8

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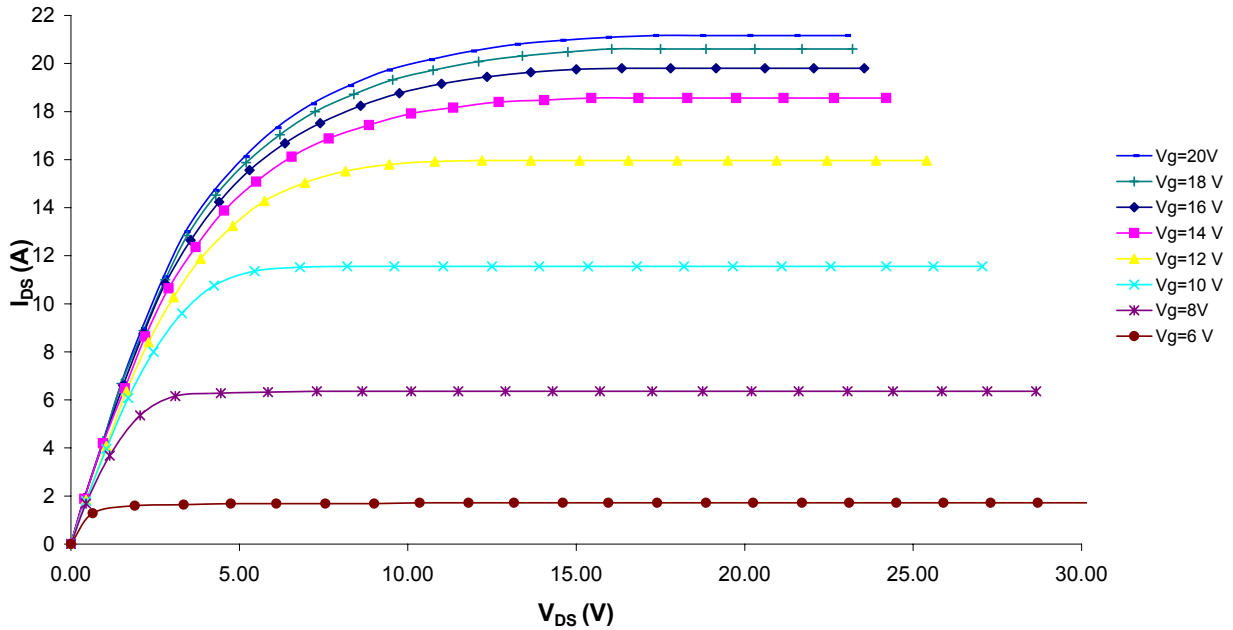


Figure 4 – Typical IV Characteristics.

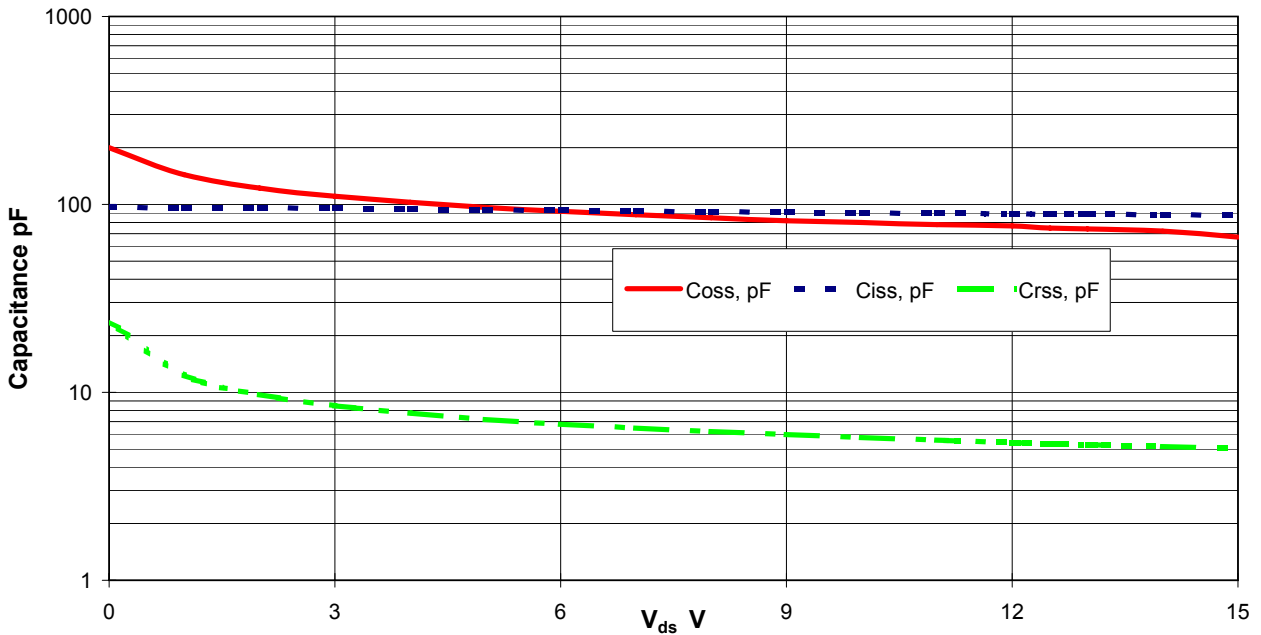
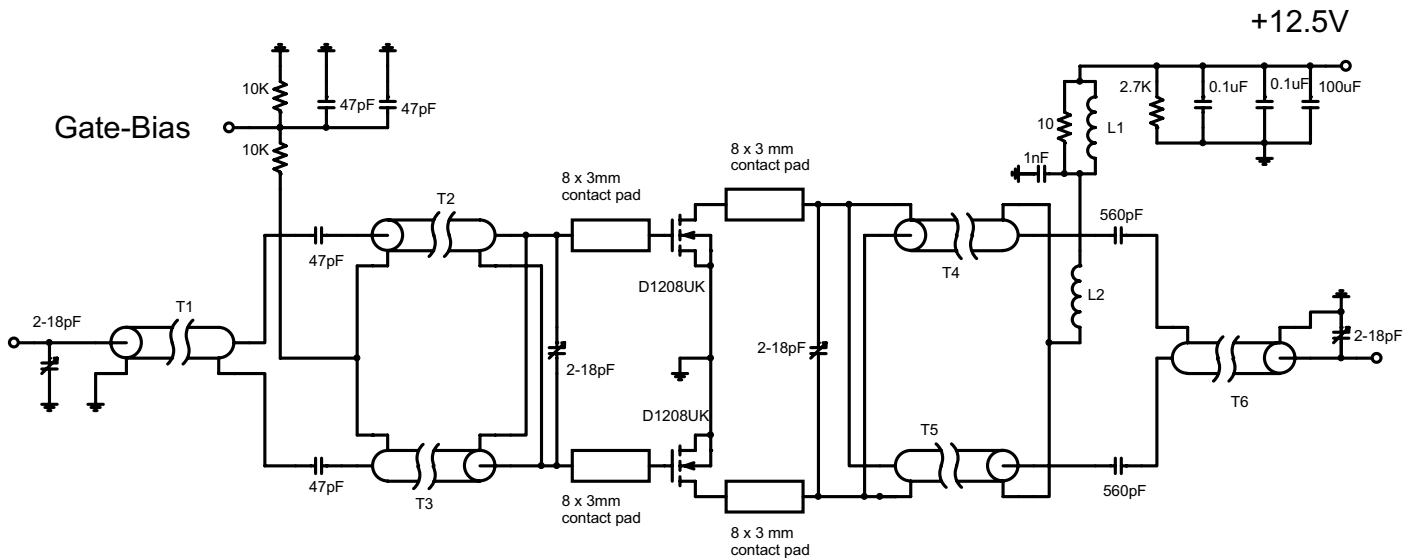


Figure 5 – Typical CV Characteristics.

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- T1 50 Ohm semi-rigid coax 0.034" dia, 7cm long
- T2,3 25 Ohm semi-rigid coax 0.070" dia, 10cm long on Siemens B62152A1X1 ferrite core
- T4,5 25 Ohm semi-rigid coax 0.070" dia, 10cm long
- T6 50 Ohm semi-rigid coax 0.034" dia, 7cm long
- L1 2.5 turns 1mm dia enamelled copper wire on Siemens B62152A1X1 ferrite core
- L2 6 turns 2 mm dia enamelled copper wire, 3.5mm internal diameter

D1208UK 400MHz Test Fixture